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## <u>TOSHIBA</u>

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOS III)

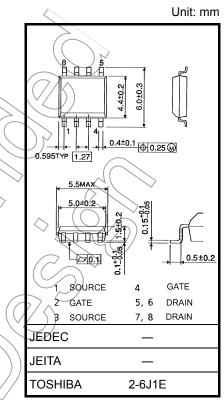
## **TPC8211**

Lithium Ion Battery Applications Portable Equipment Applications Notebook PC Applications

- Low drain-source ON-resistance:  $RDS(ON) = 25 m\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 7.0 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- Enhancement mode:  $V_{th} = 1.3$  to 2.5 V ( $V_{DS} = 10$  V,  $I_D = 1$  mA)

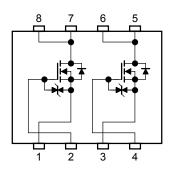
#### Absolute Maximum Ratings (Ta = 25°C)

	•	•	•	$( \square )$
Char	acteristics	Symbol	Rating	Unit
Drain-source vol	tage	V <sub>DSS</sub>	30(	y
Drain-gate voltag	ge (R <sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	30	> v
Gate-source volt	age	V <sub>GSS</sub>	±20	V
Drain current	D C (Note 1)	Ι <sub>D</sub>	5.5	A
Dialificulterit	Pulse (Note 1)	I <sub>DP</sub>	22	
Drain power dissipation	Single-device operation (Note 3a)	PD (1)	1.5	w
(t = 10 s) (Note 2a)	Single-device value at dual operation (Note 3b)	(PD(2))	1.1	
Drain power dissipation	Single-device operation (Note 3a)	PD (1)	0.75	× ×
(t = 10 s) (Note 2b)	Single-device value at dual operation (Note 3b)	→ P <sub>D (2)</sub>	0.45	vv
Single pulse ava	lanche energy (Note 4)	EAS	39.3	mJ
Avalanche curre	nt	IAR	5.5	А
Repetitive avalar Single-device va	iche energy lue at dual operation (Note 2a, 3b, 5)	EAR	0.1	mJ
Channel tempera	ature	Tch	150	°C
Storage tempera	iture range	Lstg	−55 to 150	°C



Weight: 0.085 g (typ.)

#### **Circuit Configuration**



Note: (Note 1), (Note 2), (Note 3), (Note 4) and (Note 5): See the next page.

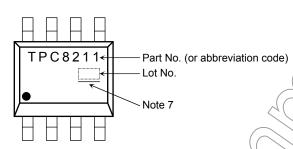
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Please handle with caution.

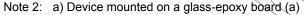
#### **Thermal Characteristics**

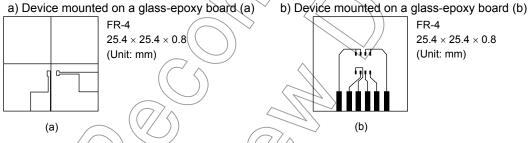
Characteristics	Symbol	Max	Unit		
Thermal resistance, channel to ambient	Single-device operation (Note 3a)	R <sub>th (ch-a) (1)</sub>	83.3		
(t = 10 s) (Note 2a)	Single-device value at dual operation (Note 3b)	R <sub>th (ch-a) (2)</sub>	114	°C/W	
Thermal resistance, channel to ambient	Single-device operation (Note 3a)	R <sub>th (ch-a) (1)</sub>	167	Civi	
(t = 10  s) (Note 2b)	Single-device value at dual operation (Note 3b)	R <sub>th (ch-a) (2)</sub>	278		

#### Marking (Note 6)



Note 1: Ensure that the channel temperature does not exceed 150°C





Note 3: a)The power dissipation and thermal resistance values are shown for a single device. (During single-device operation, power is only applied to one device.) b) The power dissipation and thermal resistance values are shown for a single device. (During dual operation, power is evenly applied to both devices.)

Note 4: 
$$V_{DD} = 24 V$$
,  $T_{ch} = 25^{\circ}C$  (initial), L = 1.0 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 5.5 A$ 

- Note 5: Repetitive rating: pulse width limited by maximum channel temperature
- Note 6: • on the lower left of the marking indicates Pin 1.

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* Weekly code:
        (Three digits)
  Week of manufacture
  (01 for first week of year, continuing up to 52 or 53)
  Year of manufacture
```

(The last digit of the calendar year)

Note 7: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

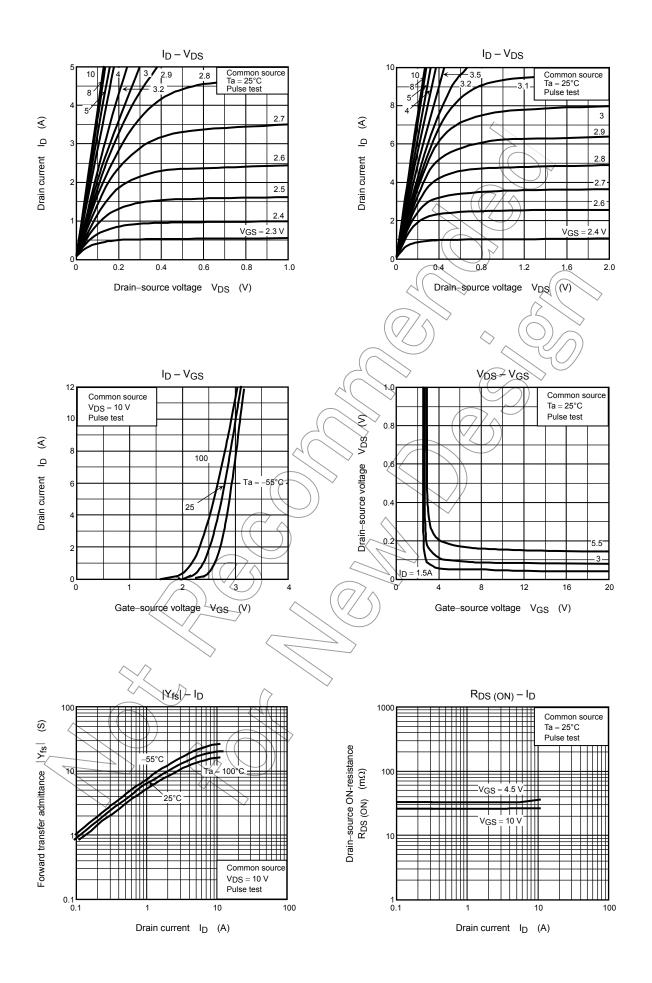
#### Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V	_	_	±10	μA
Drain cut-OFF current		I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V		_	10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D$ = 10 mA, $V_{GS}$ = 0 V	30	_	_	v
		V (BR) DSX	$I_D$ = 10 mA, $V_{GS}$ = -20 V	15	1		v
Gate threshold v	voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.3	)/-	2.5	V
Drain-source ON-resistance		R <sub>DS (ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3 A		31	44	mΩ
		R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A	$\supset$	25	36	mt2
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 A	3.5	7.0		S
Input capacitance		C <sub>iss</sub>		_	1250		
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	155	1	pF
Output capacitance		C <sub>oss</sub>			170	$\geq$	
Switching time	Rise time	tr			5	> -	
	Turn-ON time	t <sub>on</sub>	$V_{GS} \stackrel{10}{_{0}} V$		The second secon	_	ns
	Fall time	t <sub>f</sub>	U U U U U U U U U U U U U U U U U U U	$\mathbb{R}$	9		115
	Turn-OFF time	t <sub>off</sub>	Duty $\leq 1\%$ , t <sub>W</sub> = 10 $\mu$ s	) _	63	—	
Total gate charge (Gate-source plus gate-drain)		Qg		I	25		
Gate-source charge		Qgs	V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.5 Å	-	20	-	nC
Gate-drain ("miller") charge		Qgd		—	5	—	

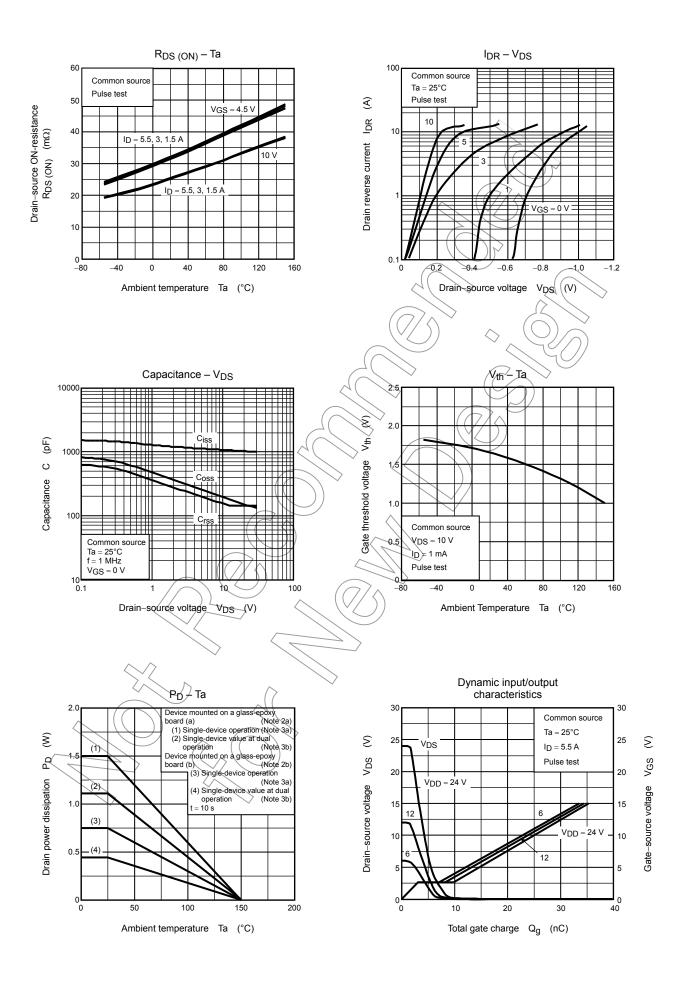
## Source-Drain Ratings and Characteristics (Ta = 25°C)

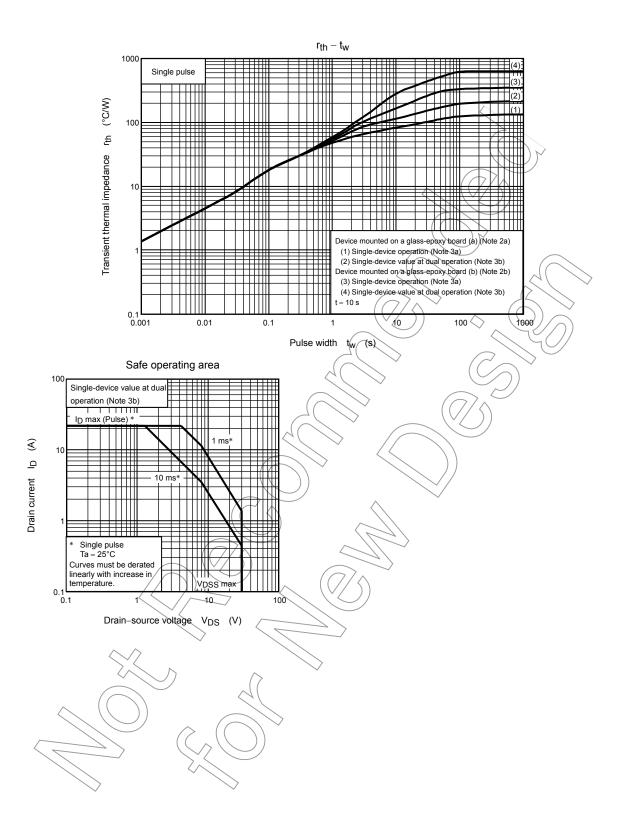
Charact	eristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)		-	_	_	22	А
Forward voltage4	(diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 5.5 A, V <sub>GS</sub> = 0 V		-	-1.2	V
		~	$\checkmark$				

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